

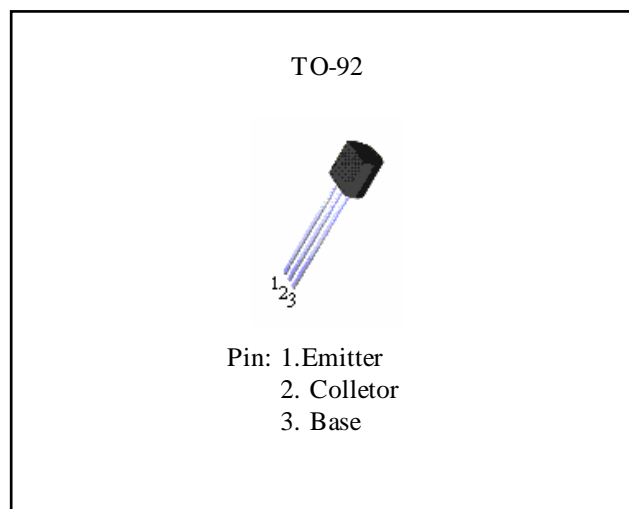
PNP Epitaxial Silicon Transistors

OUTPUT AMPLIFIER OF PORTABLE RADIO IN CLASS B PUSH-PULL OPERATION

- Complement to PJE8050
- Collector Current $I_c = -0.5A$
- Collector Dissipation $P_c = 0.625W (T_c = 25^\circ C)$

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-base Voltage	V_{EBO}	-5	V
Collector Current (DC)	I_c	-0.5	A
Collector Dissipation	P_c	0.625	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55~150	$^\circ C$



ORDERING INFORMATION

Device	Operating Temperature	Package
PJE8550CT	$-20^\circ C \sim +85^\circ C$	TO-92

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

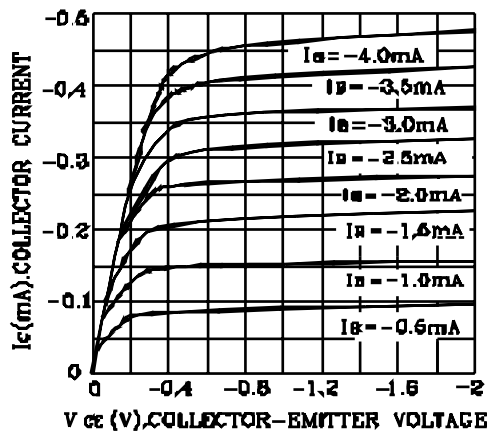
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c = -100\mu A, I_E = 0$	-20			V
Collector- Emitter Breakdown Voltage	BV_{CEO}	$I_c = -1mA, I_B = 0$	-20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -100\mu A, I_c = 0$	-5			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			-100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -3V, I_c = 0$	100		-100	nA
DC Current Gain	H_{EF1}	$V_{CE} = -1V, I_c = -50 mA$	40		400	
	H_{EF2}	$V_{CE} = -1V, I_c = -500mA$				
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_c = -500 mA, I_B = -50 mA$			-0.6	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_c = -500 mA, I_B = -50 mA$			-1.2	V
Current Gain-Bandwidth product	f_T	$V_{CE} = -10V, I_c = -50mA$		220		MHz

$h_{FE}(1)$ CLASSIFICATION

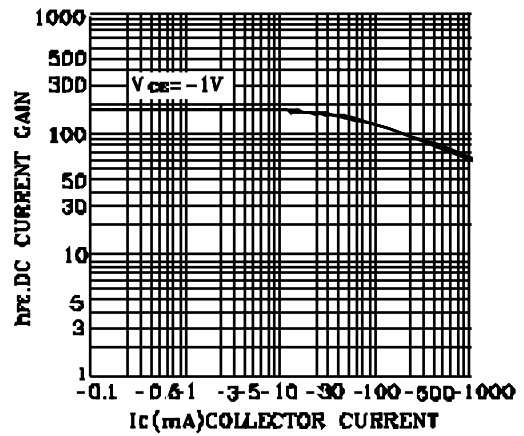
Classification	B	C	D	E
$h_{FE}(1)$	85-160	120-210	180-300	380-600

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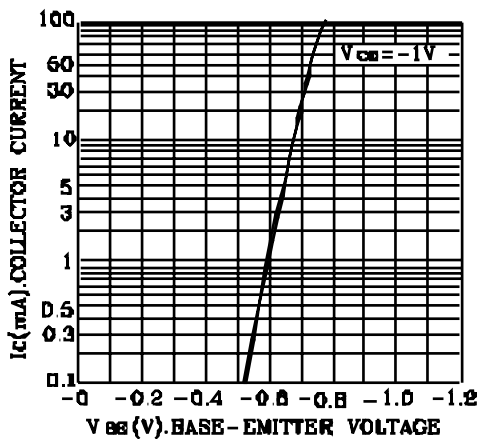
STATIC CHARACTERISTIC



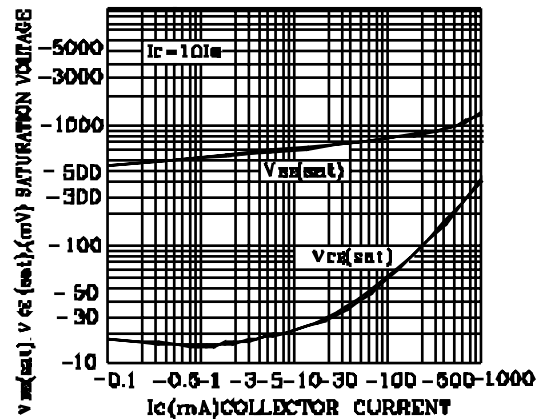
DC CURRENT GAIN



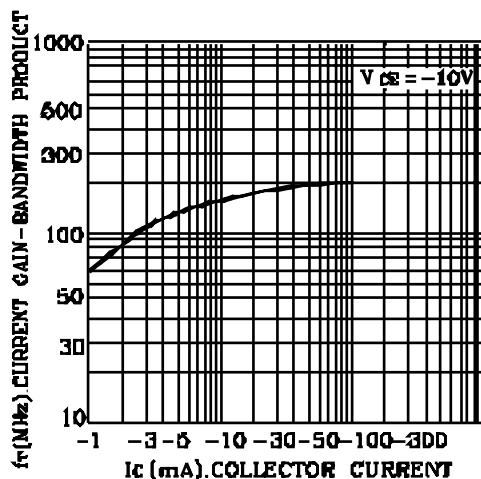
BASE-EMITTER ON VOLTAGE



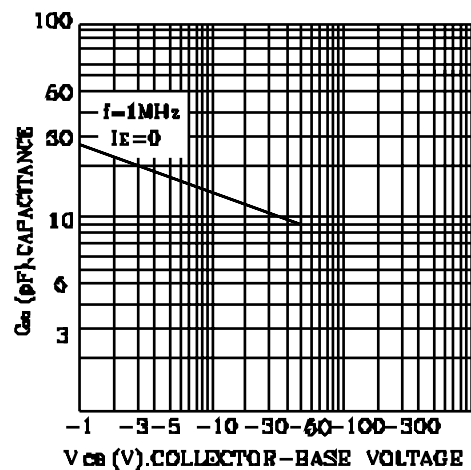
BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



CURRENT GAIN-BANDWIDTH PRODUCT



COLLECTOR OUTPUT CAPACITANCE



TO-92 Unit:mm

